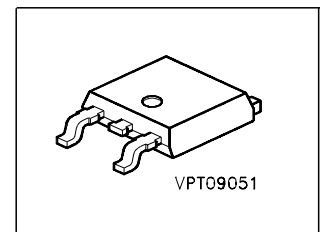


**SIPMOS® Power-Transistor**
**Features**

- P-Channel
- Enhancement mode
- Avalanche rated
- $dv/dt$  rated
- 175°C operating temperature
- ° Pb-free lead plating; RoHS compliant
- ° Qualified according to AEC Q101


**Product Summary**

Drain source voltage	$V_{DS}$	-60	V
Drain-source on-state resistance	$R_{DS(on)}$	0.075	$\Omega$
Continuous drain current	$I_D$	-30	A



<b>Pin 1</b>	<b>PIN 2/4</b>	<b>PIN 3</b>
G	D	S

<b>Type</b>	<b>Package</b>
SPD30P06P G	PG-TO252-3

**Maximum Ratings**, at  $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25\text{ °C}$ $T_C = 100\text{ °C}$	$I_D$	-30 -21.5	A
Pulsed drain current $T_C = 25\text{ °C}$	$I_{D\text{ puls}}$	-120	
Avalanche energy, single pulse $I_D = -30\text{ A}$ , $V_{DD} = -25\text{ V}$ , $R_{GS} = 25\text{ }\Omega$	$E_{AS}$	250	mJ
Avalanche energy, periodic limited by $T_{jmax}$	$E_{AR}$	12.5	
Reverse diode $dv/dt$ $I_S = -30\text{ A}$ , $V_{DS} = -48\text{ V}$ , $di/dt = 200\text{ A}/\mu\text{s}$ , $T_{jmax} = 175\text{ °C}$	$dv/dt$	6	kV/ $\mu\text{s}$
Gate source voltage	$V_{GS}$	$\pm 20$	V
Power dissipation $T_C = 25\text{ °C}$	$P_{tot}$	125	W
Operating and storage temperature	$T_j, T_{stg}$	-55...+175	$^{\circ}\text{C}$
IEC climatic category; DIN IEC 68-1		55/175/56	

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Characteristics</b>					
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.2	K/W
Thermal resistance, junction - ambient, leaded	$R_{thJA}$	-	-	100	
SMD version, device on PCB: @ min. footprint @ 6 cm <sup>2</sup> cooling area <sup>1)</sup>	$R_{thJA}$	-	-	75 50	

**Electrical Characteristics, at  $T_j = 25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Static Characteristics</b>					
Drain- source breakdown voltage $V_{GS} = 0\text{ V}$ , $I_D = -250\text{ }\mu\text{A}$	$V_{(BR)DSS}$	-60	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = -1.7\text{ mA}$	$V_{GS(th)}$	-2.1	-3	-4	
Zero gate voltage drain current $V_{DS} = -60\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_j = 25\text{ °C}$ $V_{DS} = -60\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_j = 150\text{ °C}$	$I_{DSS}$	-	-0.1 -10	-1 -100	$\mu\text{A}$
Gate-source leakage current $V_{GS} = -20\text{ V}$ , $V_{DS} = 0\text{ V}$	$I_{GSS}$	-	-10	-100	nA
Drain-source on-state resistance $V_{GS} = -10\text{ V}$ , $I_D = -21.5\text{ A}$	$R_{DS(on)}$	-	0.069	0.075	$\Omega$

<sup>1</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical without blown air.

**Electrical Characteristics, at  $T_j = 25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Dynamic Characteristics</b>					
Transconductance $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = -21.5\text{ A}$	$g_{fs}$	5.2	10.4	-	S
Input capacitance $V_{GS} = 0\text{ V}$ , $V_{DS} = -25\text{ V}$ , $f = 1\text{ MHz}$	$C_{iss}$	-	1228	1535	pF
Output capacitance $V_{GS} = 0\text{ V}$ , $V_{DS} = -25\text{ V}$ , $f = 1\text{ MHz}$	$C_{oss}$	-	387	383	
Reverse transfer capacitance $V_{GS} = 0\text{ V}$ , $V_{DS} = -25\text{ V}$ , $f = 1\text{ MHz}$	$C_{rss}$	-	142	177	
Turn-on delay time $V_{DD} = -30\text{ V}$ , $V_{GS} = -10\text{ V}$ , $I_D = -21.5\text{ A}$ , $R_G = 1.6\text{ }\Omega$	$t_{d(on)}$	-	13	19.5	ns
Rise time $V_{DD} = -30\text{ V}$ , $V_{GS} = -10\text{ V}$ , $I_D = -21.5\text{ A}$ , $R_G = 1.6\text{ }\Omega$	$t_r$	-	11	16.5	
Turn-off delay time $V_{DD} = -30\text{ V}$ , $V_{GS} = -10\text{ V}$ , $I_D = -21.5\text{ A}$ , $R_G = 1.6\text{ }\Omega$	$t_{d(off)}$	-	30	45	
Fall time $V_{DD} = -30\text{ V}$ , $V_{GS} = -10\text{ V}$ , $I_D = -21.5\text{ A}$ , $R_G = 1.6\text{ }\Omega$	$t_f$	-	20	30	

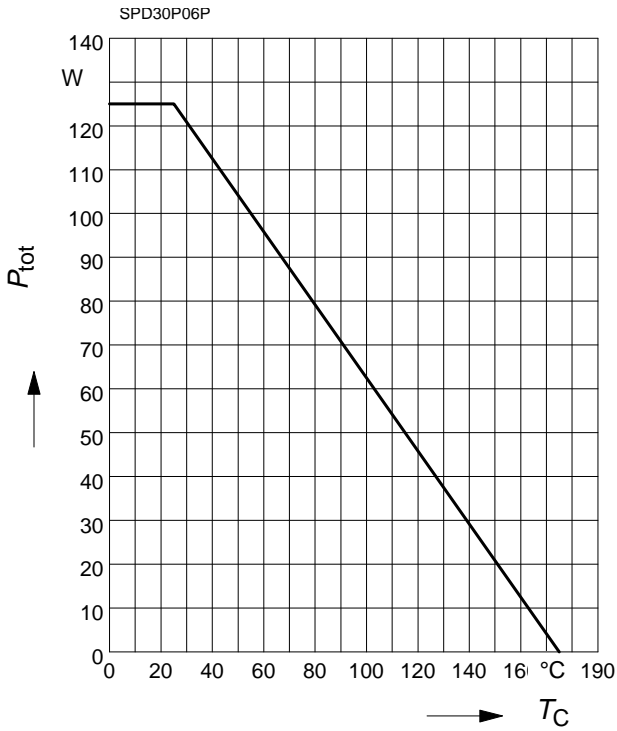
**Electrical Characteristics, at  $T_j = 25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Dynamic Characteristics</b>					
Gate to source charge $V_{DD} = -48\text{ V}, I_D = -30\text{ A}$	$Q_{gs}$	-	3.7	5.6	nC
Gate to drain charge $V_{DD} = -48\text{ V}, I_D = -30\text{ A}$	$Q_{gd}$	-	13.8	20.7	
Gate charge total $V_{DD} = -48\text{ V}, I_D = -30\text{ A}, V_{GS} = 0\text{ to }-10\text{ V}$	$Q_g$	-	32	48	
Gate plateau voltage $V_{DD} = -48\text{ V}, I_D = -30\text{ A}$	$V_{(plateau)}$	-	-5.2	-	V

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Reverse Diode</b>					
Inverse diode continuous forward current $T_C = 25\text{ °C}$	$I_S$	-	-	-30	A
Inverse diode direct current, pulsed $T_C = 25\text{ °C}$	$I_{SM}$	-	-	-120	
Inverse diode forward voltage $V_{GS} = 0\text{ V}, I_F = -30$	$V_{SD}$	-	-1.3	-1.7	V
Reverse recovery time $V_R = -30\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$	$t_{rr}$	-	64.6	97	ns
Reverse recovery charge $V_R = -30\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$	$Q_{rr}$	-	153	230	nC

**Power dissipation**

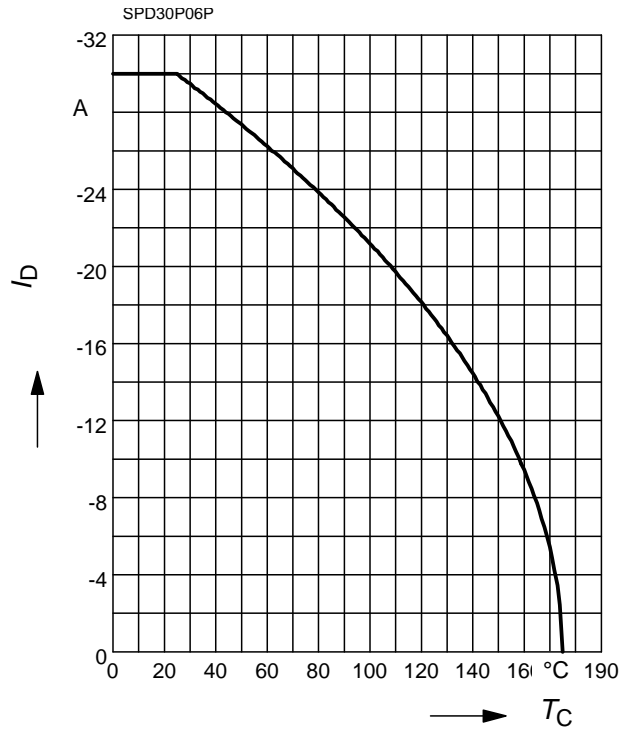
$$P_{tot} = f(T_C)$$



**Drain current**

$$I_D = f(T_C)$$

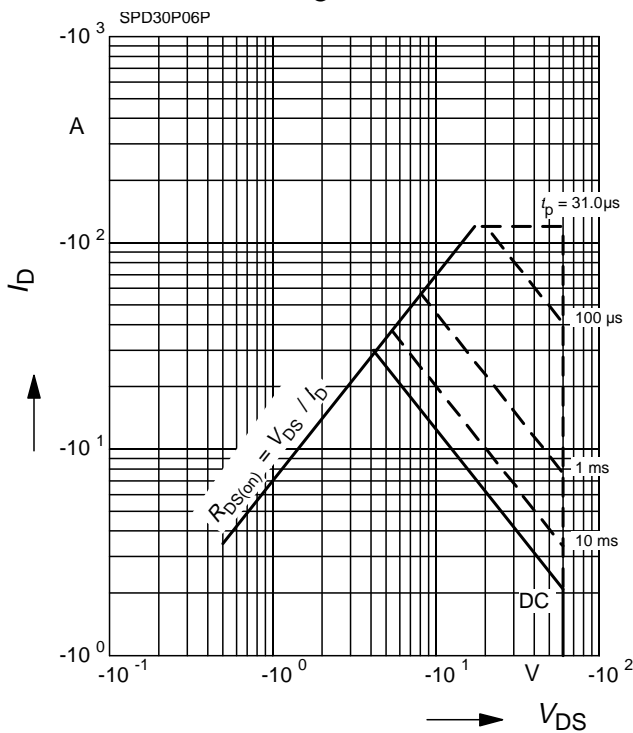
parameter:  $V_{GS} \geq 10 \text{ V}$



**Safe operating area**

$$I_D = f(V_{DS})$$

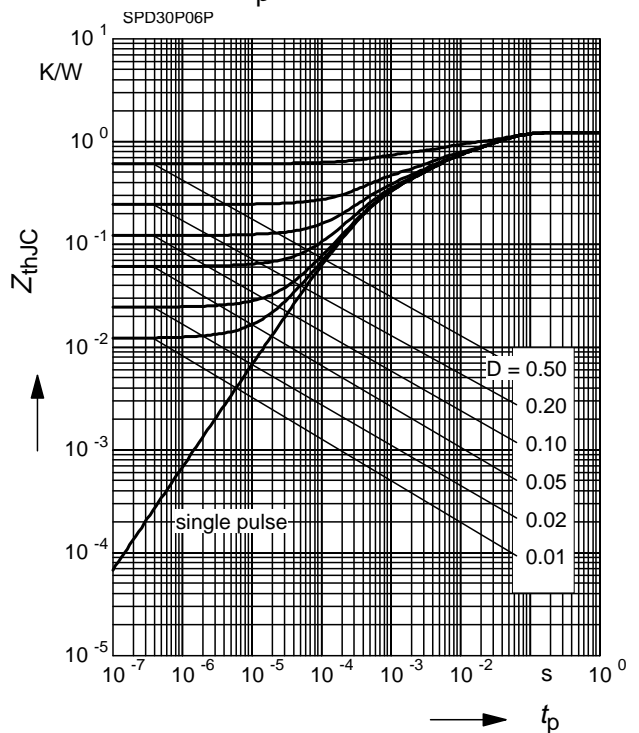
parameter:  $D = 0, T_C = 25 \text{ °C}$



**Transient thermal impedance**

$$Z_{thJC} = f(t_p)$$

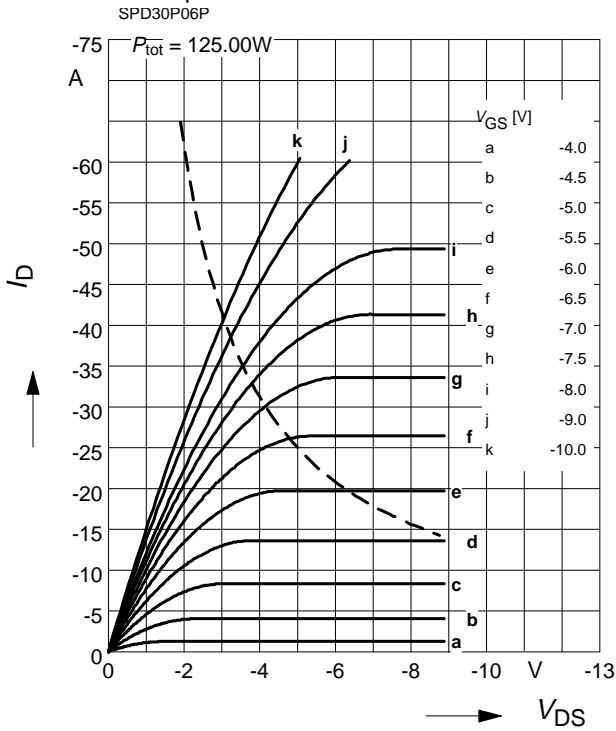
parameter:  $D = t_p / T$



**Typ. output characteristic**

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

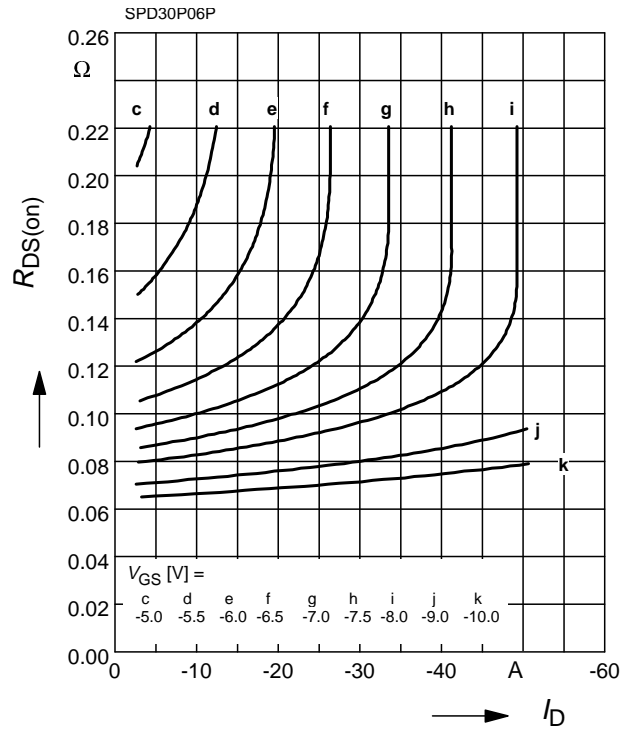
parameter:  $t_p = 80 \mu\text{s}$



**Typ. drain-source-on-resistance**

$R_{DS(on)} = f(I_D)$

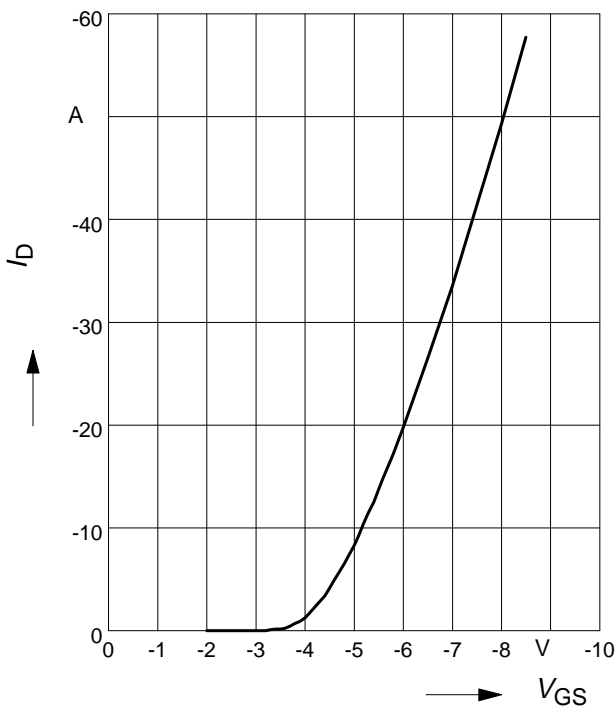
parameter:  $V_{GS}$



**Typ. transfer characteristics  $I_D = f(V_{GS})$**

$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

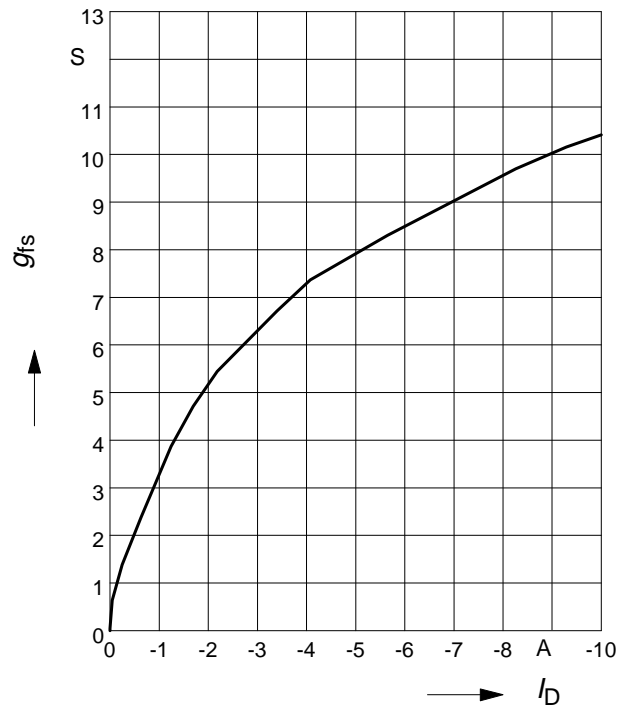
parameter:  $t_p = 80 \mu\text{s}$



**Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$

parameter:  $g_{fs}$

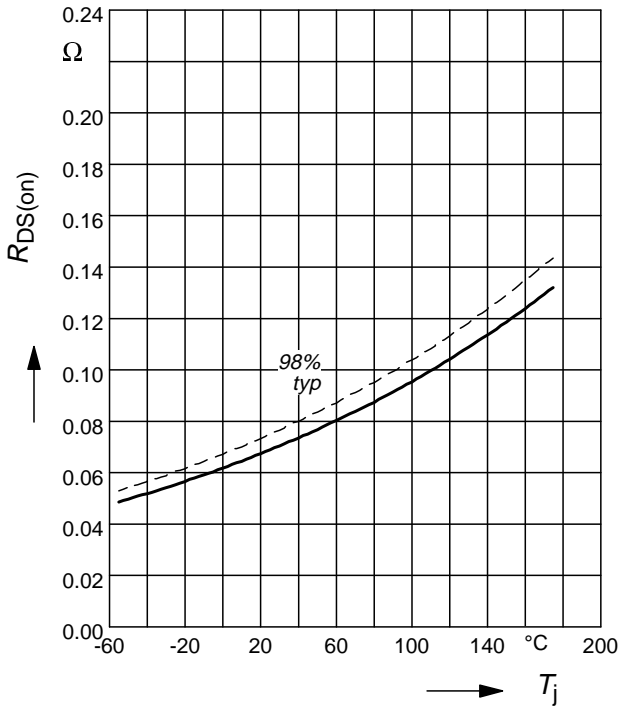


**Drain-source on-state resistance**

$$R_{DS(on)} = f(T_j)$$

parameter:  $I_D = -21.5 \text{ A}$ ,  $V_{GS} = -10 \text{ V}$

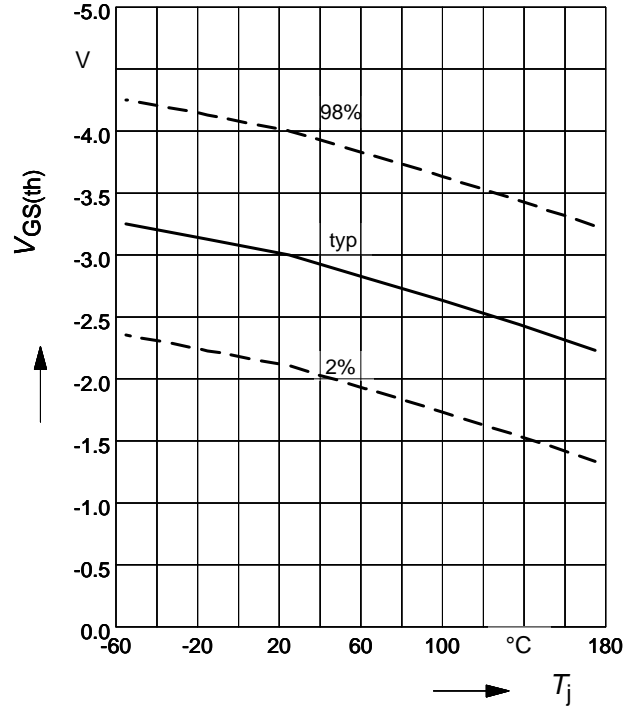
SPD30P06P



**Gate threshold voltage**

$$V_{GS(th)} = f(T_j)$$

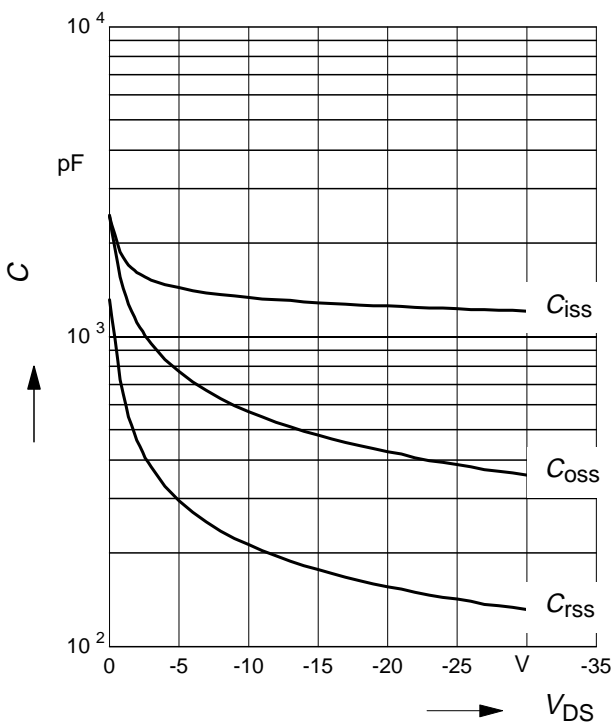
parameter:  $V_{GS} = V_{DS}$ ,  $I_D = -1.7 \text{ mA}$



**Typ. capacitances**

$$C = f(V_{DS})$$

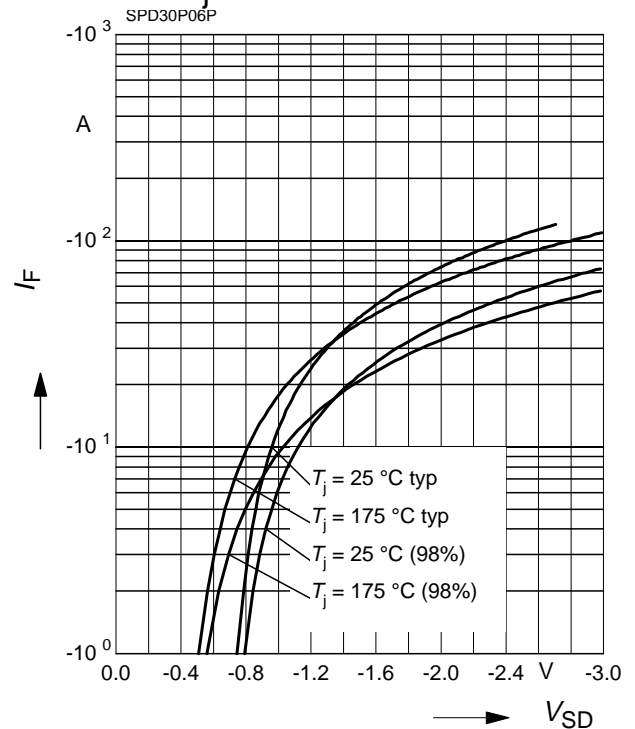
parameter:  $V_{GS}=0\text{V}$ ,  $f=1 \text{ MHz}$



**Forward characteristics of reverse diode**

$$I_F = f(V_{SD})$$

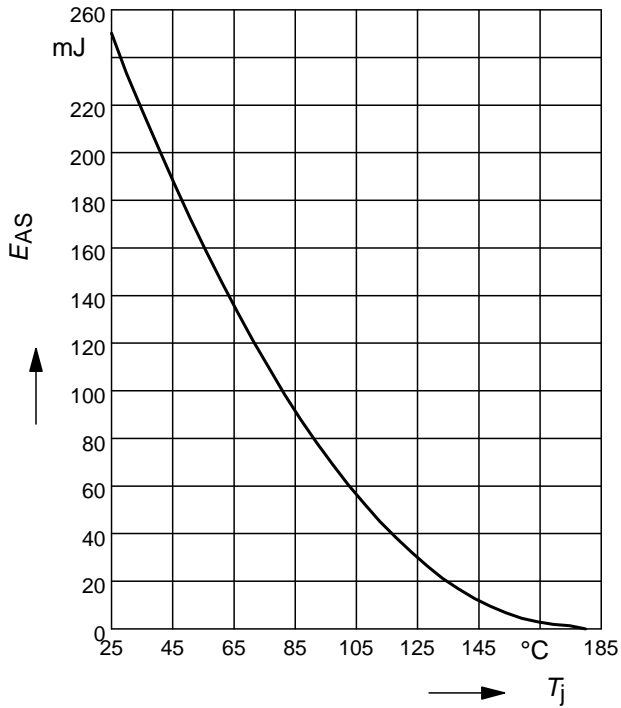
parameter:  $T_j$ ,  $t_p = 80 \mu\text{s}$



**Avalanche energy**

$$E_{AS} = f(T_j)$$

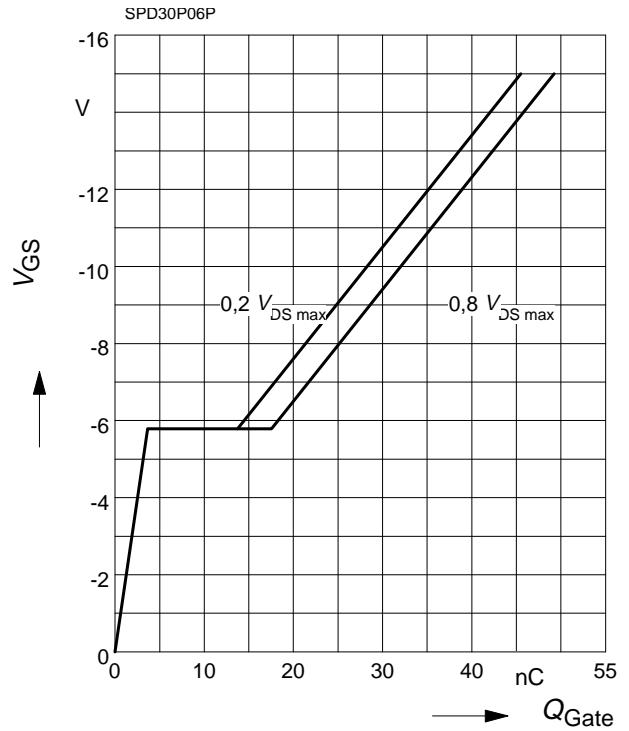
para.:  $I_D = -30\text{ A}$  ,  $V_{DD} = -25\text{ V}$  ,  $R_{GS} = 25\ \Omega$



**Typ. gate charge**

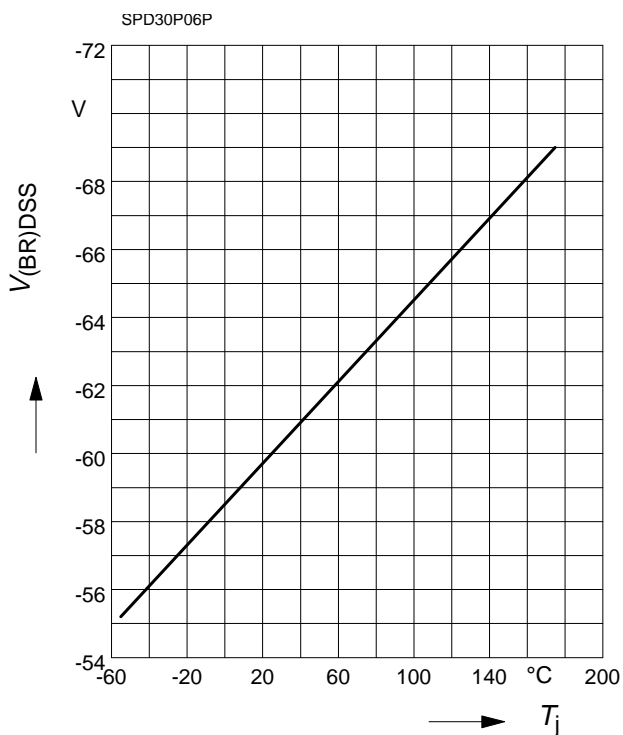
$$V_{GS} = f(Q_{Gate})$$

parameter:  $I_D = -30\text{ A}$  pulsed



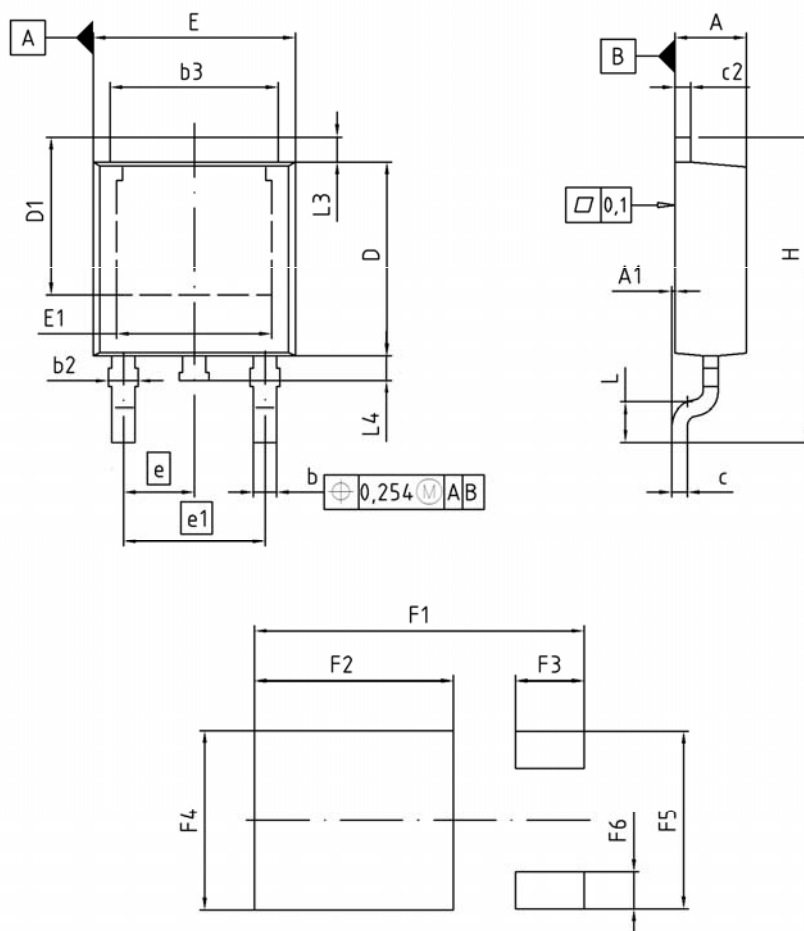
**Drain-source breakdown voltage**

$$V_{(BR)DSS} = f(T_j)$$





Package outline: PG-TO252-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	5.00	5.50	0.197	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.98	0.018	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.40	6.73	0.252	0.265
E1	4.70	5.21	0.185	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L3	0.90	1.25	0.035	0.049
L4	0.51	1.00	0.020	0.039
F1	10.50	10.70	0.413	0.421
F2	6.30	6.50	0.248	0.256
F3	2.10	2.30	0.083	0.091
F4	5.70	5.90	0.224	0.232
F5	5.66	5.86	0.223	0.231
F6	1.10	1.30	0.043	0.051

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